XN01116 (XN1116)

Silicon PNP epitaxial planar type

For switching/digital circuits

Features

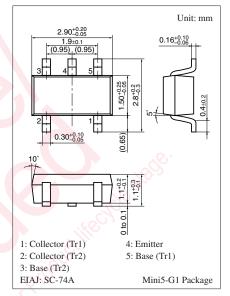
- Two elements incorporated into one package (Emitter-coupled transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

Basic Part Number

• UNR2116 (UN2116) × 2

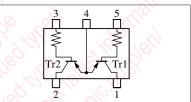
Absolute Maximum Ratings $T_a = 25^{\circ}C$

| Symbol | Rating | Unit | |
|------------------|--|---|--|
| V _{CBO} | -50 | V | |
| V _{CEO} | -50 | V | |
| I _C | -100 | mA | |
| P _T | 300 | mW | |
| Tj | 150 | °C | |
| T _{stg} | -55 to +150 | °C | |
| | V _{CBO} V _{CEO} I _C P _T T _j | $\begin{array}{c c} V_{CBO} & -50 \\ \hline V_{CEO} & -50 \\ \hline I_C & -100 \\ \hline P_T & 300 \\ \hline T_j & 150 \\ \hline \end{array}$ | |



Marking Symbol: 7N

Internal Connection



Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

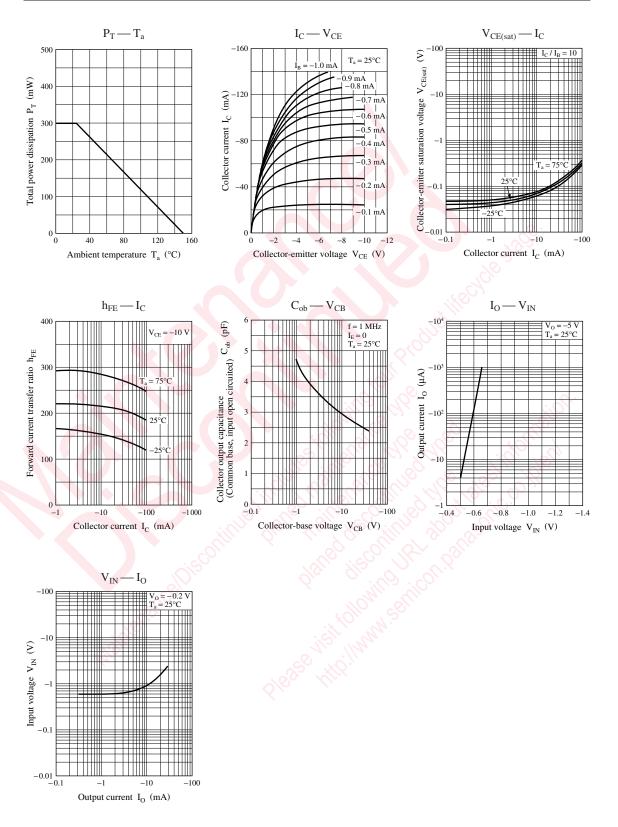
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--|----------------------------------|---|------|------|--------|------|
| Collector-base voltage (Emitter open) | V _{CBO} | $I_{\rm C} = -10 \ \mu \text{A}, I_{\rm E} = 0$ | -50 | | | V |
| Collector-emitter voltage (Base open) | V _{CEO} | $I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$ | -50 | | | V |
| Collector-base cutoff current (Emitter open) | I _{CBO} | $V_{CB} = -50 \text{ V}, I_E = 0$ | | | - 0.1 | μΑ |
| Collector-emitter cutoff current (Base open) | I _{CEO} | $V_{CE} = -50 \text{ V}, I_B = 0$ | | | - 0.5 | μΑ |
| Emitter-base cutoff current (Collector open) | I _{EBO} | $V_{EB} = -6 V, I_C = 0$ | | | - 0.01 | mA |
| Forward current transfer ratio | h _{FE} | $V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$ | 160 | | 460 | _ |
| h _{FE} Ratio * | h _{FE(Small} /Large) | $V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$ | 0.50 | 0.99 | | — |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -0.3 \text{ mA}$ | | | - 0.25 | V |
| Output voltage high-level | V _{OH} | $V_{CC} = -5 \text{ V}, V_B = -0.5 \text{ V}, R_L = 1 \text{ k}\Omega$ | -4.9 | | | V |
| Output voltage low-level | V _{OL} | $V_{CC} = -5 \text{ V}, \text{V}_{\text{B}} = -2.5 \text{V}, \text{R}_{\text{L}} = 1 \text{k} \Omega$ | | | - 0.2 | V |
| Input resistance | R ₁ | | -30% | 4.7 | +30% | kΩ |
| Transition frequency | f _T | $V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$ | | 80 | | MHz |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: Ratio between 2 elements

Note) The part number in the parenthesis shows conventional part number.

XN01116





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